## STEP-UP DC/DC CONVERTER with SHUTDOWN FUNCTION

NO.EA-255-230823

## OUTLINE

The R1202x Series are CMOS-based PWM step-up DC/DC converter ICs with low supply current.
Each of these ICs consists of an NMOS FET, NPN transistor, an oscillator, a PWM comparator, a voltage reference unit, an error amplifier, a current limit circuit, an under voltage lockout circuit (UVLO), an over-voltage protection circuit (OVP), a soft-start circuit, a Maxduty limit circuit, and a thermal shutdown protection circuit. By simply using an inductor, a resistor, and capacitors as external components, a high-efficiency step-up DC/DC converter can be easily configured. At the standby mode, a rectifier transistor can separate the output from the input.

The R1202x Series include a thermal shut-down circuit and an under-voltage lockout circuit (UVLO) which separate the output from the input to shut down the current when the overheat caused when the output is connected to the Gnd is detected and also during the UVLO detection. As other protection functions, the R1202x Series contain a cycle by cycle current limit circuit that limits the Lx peak current, and an over-voltage protection circuit (OVP) that detects the output overvoltage.

The R1202x Series offer three versions: the R1202xxxxA/B versions, which are optimized for constant-voltage power supply and the R1202xxxxD version, which is optimized to drive serial white LEDs with constant current. While the R1202xxxxA version discharges the Vout output to OV at the shutdown, the R1202xxxxB version doesn't. The brightness of the white LEDs can be adjusted quickly by applying a PWM signal ( 200 Hz to 300 kHz ) to the CE pin.

The R1202x Series are available in DFN1616-6B and TSOT-23-6 packages.

## FEATURES

```
- Input Voltage Range
2.3V to 5.5V (R1202xxxxA/B)
1.8V to 5.5V (R1202xxxxD)
- Supply Current .......................................... Typ. 800\muA
- Standby Current. Max. \(5 \mu \mathrm{~A}\)
- Feedback Voltage \(1.0 \mathrm{~V} \pm 15 \mathrm{mV}(\mathrm{R} 1202 x x x x \mathrm{~A} / \mathrm{B})\) \(0.2 \mathrm{~V} \pm 10 \mathrm{mV}(\mathrm{R} 1202 \mathrm{xxxxD})\)
- Oscillator Frequency
Typ. 1.2MHz
- Maximum Duty Cycle
Typ. 91\%
- UVLO Function ............................................. Typ.2.0V (Hys.Typ.0.2V) (R1202xxxxA/B)
Typ.1.6V (Hys.Typ.0.1V) (R1202xxxxD)
- Lx Current Limit Function................................ Select from 350mA, 700mA
- Over Voltage Protection ................................... Select from 14V-23V (Refer the Selection Guide)
- LED dimming control for R1202xxxxD ............. by external PWM signal (Frequency 200 Hz to 300 kHz )
- Thermal Protection Function ......................... Typ. \(150^{\circ} \mathrm{C}\) (Hys.Typ. \(50^{\circ} \mathrm{C}\) )
- Built-in Auto Discharge Function...................... R1202xxxxA
- NMOS ON Resistance ...................................... \(1.35 \Omega\)
- Packages ......................................................... DFN1616-6B, TSOT-23-6
```


## APPLICATION

- Constant Voltage Power Source for portable equipment
- OLED power supply for portable equipment
- White LED Backlight for portable equipment


## SELECTION GUIDE

The OVP threshold voltage, current limit, package and $V_{F B} /$ Auto discharge are user-selectable options.

| Product Name | Package | Quantity per Reel | Pb Free | Halogen Free |
| :--- | :---: | :---: | :---: | :---: |
| R1202Lyz1*-TR | DFN1616-6B | $5,000 \mathrm{pcs}$ | Yes | Yes |
| R1202Nyz3*-TR-FE | TSOT-23-6 | $3,000 \mathrm{pcs}$ | Yes | Yes |

$y$ : Designation of OVP threshold
(3) $14 \mathrm{~V}: R 1202 x x x x A / B / D$
(4) $17 \mathrm{~V}: \mathrm{R} 1202 x x x x A / B$
(5) $19 \mathrm{~V}: \mathrm{R} 1202 x x x x A / B$
(6) $21 \mathrm{~V}: \mathrm{R} 1202 x x x x A / B$
(7) $23 \mathrm{~V}: R 1202 x x x x A / B / D$
z : Designation of current limit
(1) 350 mA
(2) 700 mA

* : Designation of VFB, auto discharge function

|  | VFB | Auto discharge |
| :---: | :---: | :---: |
| A | 1.0 V | $\bigcirc$ |
| $B$ | 1.0 V | $\times$ |
| D | 0.2 V | $\times$ |

Auto-discharge function quickly lowers the output voltage to 0 V , when the chip enable signal is switched from the active mode to the standby mode, by releasing the electrical charge accumulated in the external capacitor.

## BLOCK DIAGRAMS




## PIN DESCRIPTIONS

- DFN1616-6B

Top View


Bottom View


TSOT-23-6


DFN1616-6B

| Pin No | Symbol | Pin Description |
| :---: | :---: | :--- |
| 1 | CE | Chip Enable Pin ("H" Active) |
| 2 | VFB $_{\text {FB }}$ | Feedback Pin |
| 3 | Lx | Switching Pin (Open Drain Output) |
| 4 | GND | Ground Pin |
| 5 | VIN $^{\text {Vout }}$ | Input Pin |
| 6 | Output Pin |  |

*) The tab is substrate level (GND). The tab is better to be connected to the GND, but leaving it open is also acceptable.

TSOT-23-6

| Pin No | Symbol | Pin Description |
| :---: | :---: | :--- |
| 1 | CE | Chip Enable Pin ("H" Active) |
| 2 | Vout | Output Pin |
| 3 | Vin | Input Pin |
| 4 | Lx | Switching Pin (Open Drain Output) |
| 5 | GND | Ground Pin |
| 6 | VFB $^{2}$ | Feedback Pin |


| ABSOLUTE MAXIMUM RATINGS |  |  |  | $\frac{(\mathrm{GND}=0 \mathrm{~V})}{\text { Unit }}$ |
| :---: | :---: | :---: | :---: | :---: |
| Symbol |  | Item | Rating |  |
| Vin | VIN Pin Voltage |  | -0.3 to 6.5 | V |
| $V_{\text {ce }}$ | CE Pin Voltage |  | -0.3 to 6.5 | V |
| $V_{\text {fb }}$ | $V_{\text {Fb }}$ Pin Voltage |  | -0.3 to 6.5 | V |
| Vout | Vout Pin Voltage |  | -0.3 to 25 | V |
| VLx | Lx Pin Voltage |  | -0.3 to 25 | V |
| ILx | Lx Pin Current |  | 1000 | mA |
| Po | Power Dissipation * | DFN1616-6B <br> (JEDEC STD. 51-7 Test Land Pattern) | 2400 | mW |
|  |  | TSOT-23-6 (Standard Test Land Pattern) | 460 |  |
| Tj | Junction Temperature Range |  | -40 to 125 | ${ }^{\circ} \mathrm{C}$ |
| Tstg | Storage Temperature Range |  | -55 to 125 | ${ }^{\circ} \mathrm{C}$ |

*) Refer to POWER DISSIPATION for detailed information.

## ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Item | Rating |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Vin | Oprest | R1202xxxxA/B | 2.3 V to 5.5 V | V |
| Vin | Operating Input Voltage | R1202xxxxD | 1.8 V to 5.5 V | V |
| Ta | Operating Temperature Range | -40 to 85 |  | ${ }^{\circ} \mathrm{C}$ |

## RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

## ELECTRICAL CHARACTERISTICS

R1202x


| Symbol | Item | Conditions |  | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maxduty | Maximum Duty Cycle | $\mathrm{V}_{\mathrm{I}}=3.6 \mathrm{~V}, \mathrm{~V}_{\text {FB }}=0 \mathrm{~V}$ |  | 86 | 91 |  | \% |
| Vovp1 | OVP Detect Voltage | $\mathrm{V}_{\mathrm{IN}}=3.6 \mathrm{~V} \text {, }$ <br> Vout rising | R1202x3xxA/B/D | 13.2 | 14 | 14.8 | V |
|  |  |  | R1202x4xxA/B | 16.2 | 17 | 17.8 |  |
|  |  |  | R1202x5xxA/B | 18.2 | 19 | 19.8 |  |
|  |  |  | R1202x6xxA/B | 20.2 | 21 | 21.8 |  |
|  |  |  | R1202x7xxA/B/D | 22.2 | 23 | 23.8 |  |
| Vovp2 | OVP Release Voltage | $\mathrm{V}_{\mathrm{IN}}=3.6 \mathrm{~V} \text {, }$ <br> Vout falling | R1202x3xxA/B/D |  | $\begin{gathered} \hline \text { Vovp1 } \\ -1.1 \end{gathered}$ |  | V |
|  |  |  | R1202x4xxA/B |  | $\begin{aligned} & \hline \text { Vovp1 } \\ & -1.3 \end{aligned}$ |  |  |
|  |  |  | R1202x5xxA/B |  | $\begin{aligned} & \hline \text { Vovp1 } \\ & -1.4 \end{aligned}$ |  |  |
|  |  |  | R1202x6xxA/B |  | $\begin{aligned} & \hline \text { Vovp1 } \\ & -1.5 \end{aligned}$ |  |  |
|  |  |  | R1202x7xxA/B/D |  | $\begin{aligned} & \text { Vovp1 } \\ & -1.7 \end{aligned}$ |  |  |
| TTsd | Thermal Shutdown Detect Temperature | $\mathrm{V}_{1 \times}=3.6 \mathrm{~V}$ |  |  | 150 |  | ${ }^{\circ} \mathrm{C}$ |
| TTsR | Thermal Shutdown Release Temperature | $\mathrm{V}_{1 \times}=3.6 \mathrm{~V}$ |  |  | 100 |  | ${ }^{\circ} \mathrm{C}$ |

## THEORY OF OPERATION

## Operation of Step-Up DC/DC Converter and Output Current <br> <Basic Circuit>


<Current through L>


There are two operation modes of the step-up PWM control-DC/DC converter. That is the continuous mode and discontinuous mode by the continuousness inductor.

When the transistor turns ON, the voltage of inductor $L$ becomes equal to $V$ in voltage. The increase value of inductor current (i1) will be

$$
\Delta \mathrm{i} 1=\mathrm{V}_{\mathrm{IN}} \times \text { ton } / \mathrm{L}
$$

Formula 1

As the step-up circuit, during the OFF time (when the transistor turns OFF) the voltage is continually supply from the power supply. The decrease value of inductor current (i2) will be
$\qquad$

$$
\Delta \mathrm{i} 2=\left(\mathrm{V}_{\text {out }}-\mathrm{V}_{\text {IN }}\right) \times \text { topen } / \mathrm{L} .
$$

At the PWM control-method, the inductor current become continuously when topen=toff, the DC/DC converter operate as the continuous mode.

In the continuous mode, the variation of current of i1 and i2 is same at regular condition.

$$
\text { VIN } \times \text { ton / L = (Vout - Vin }) \times \text { toff / L .................................................................................... Formula } 3
$$

The duty at continuous mode will be

$$
\text { duty }(\%)=\text { ton / (ton + toff) }=(\text { Vout - Viv }) / \text { Vout .................................................................. Formula } 4
$$

The average of inductor current at $\mathrm{tf}=$ toff will be

$$
\text { IL(Ave.) = VIN } \times \text { ton / }(2 \times \mathrm{L}) \text {............................................................................................. Formula } 5
$$

If the input voltage $=$ output voltage, the lout will be

$$
\begin{aligned}
& \text { lout }=\mathrm{V}_{\text {IN }}{ }^{2} \times \text { ton } /(2 \times \mathrm{L} \times \text { Vout }) \\
& \text { Formula } 6
\end{aligned}
$$

If the lout value is large than above the calculated value (Formula 6), it will become the continuous mode, at this status, the peak current (ILmax) of inductor will be

$$
\begin{aligned}
& \text { ILmax }=\text { lout } \times \text { Vout } / \mathrm{V}_{\text {IN }}+\mathrm{V}_{\text {IN }} \times \mathrm{T} \times\left(\mathrm{V}_{\text {OUT }}-\mathrm{V}_{\text {IN }}\right) /\left(2 \times \mathrm{L} \times \mathrm{V}_{\text {OUT }}\right) \\
& \text { Formula } 8
\end{aligned}
$$

The peak current value is larger than the lout value. In case of this, selecting the condition of the input and the output and the external components by considering of ILmax value.
The explanation above is based on the ideal calculation, and the loss caused by Lx switch and the external components are not included.
The actual maximum output current will be between $50 \%$ and $80 \%$ by the above calculations. Especially, when the IL is large or $\mathrm{V}_{\mathrm{IN}}$ is low, the loss of $\mathrm{V}_{\mathrm{IN}}$ is generated with on resistance of the switch. Moreover, it is necessary to consider Vf of the diode (approximately 0.8 V ) about Vout.

## Soft-Start

## R1202xxxxA/B

After inputting " H " to the CE pin, the error amplifier in the DC/DC converter starts from OV and slowly rises with a time (typ. 2ms) until the set output voltage is reached.
However, immediately after startup, (the input voltage ( $\mathrm{V}_{\mathrm{IN}}$ ) - NPN Forward voltage) is output without the soft start control.

## R1202xxxxD

By gradually increasing the duty of the PWM signal input to the CE pin, the LED current (luminance) can be slowly increased in the same way as the soft start operation.

## Protect Function

If the over current is detected, internal mosfet will turn-off soon. At the next operating period, mosfet will turn-on again and continue to watch the current.
The UVLO function and the thermal shutdown function are turned off the NMOS-driver and NPN-transister when the $\mathrm{V}_{\mathbb{N}}$ decreases more than the UVLO detect threshold voltage or the inside of IC exceeds the thermal shutdown detect temperature, and reset IC when the Vin rises more than the UVLO release voltage or the inside of IC falls below the thermal shutdown release temperature, and restart the operation.

## Shutdown

At standby mode, the output is completely separated from the input and shutdown by the NPN transistor of internal IC. However, the leakage current is generated when the $L_{x}$ pin voltage is higher than Vin pin voltage at standby mode.
R1202xxxxA (with auto discharge function): In the term of standby mode, the switch between Vout to GND is turned ON and output capacitor is discharged.

## APPLICATION INFORMATION

Typical Applications


R1202xxxxA/B


R1202xxxxD

## - Selection of Inductor

The peak current of the inductor at normal mode can be estimated as the next formula when the efficiency is $80 \%$.

$$
\text { ILmax }=1.25 \times \text { lout } \times \text { Vout } / \text { Vin }+0.5 \times \text { ViN } \times\left(\text { Vout }-\mathrm{V}_{\text {IN }}\right) /(\mathrm{L} \times \mathrm{Vout} \times \text { fosc })
$$

In the case of start-up or dimming control by CE pin, inductor transient current flows, and the peak current of it must be equal or less than the current limit of the IC. The peak current should not beyond the rated current of the inductor. The recommended inductance value is $10 \mu \mathrm{H}-22 \mu \mathrm{H}$.

Table 1 Peak current value in each condition

| Condition |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IN }}(\mathrm{V})$ | Vout $^{(\mathrm{V})}$ | lout $(\mathrm{mA})$ | $\mathrm{L}(\mu \mathrm{H})$ | ILmax (mA) |
| 3 | 14 | 20 | 10 | 215 |
| 3 | 14 | 20 | 22 | 160 |
| 3 | 21 | 20 | 10 | 280 |
| 3 | 21 | 20 | 22 | 225 |

Table 2 Recommended inductors

| $\mathbf{L}(\mu \mathrm{H})$ | Part No. | Rated current (mA) | Size (mm) |
| :---: | :---: | :---: | :---: |
| 10 | LQH32CN100K53 | 450 | $3.2 \times 2.5 \times 1.55$ |
| 10 | LQH2MC100K02 | 225 | $2.0 \times 1.6 \times 0.9$ |
| 10 | VLF3010A-100 | 490 | $2.8 \times 2.6 \times 0.9$ |
| 10 | VLS252010-100 | 520 | $2.5 \times 2.0 \times 1.0$ |
| 10 | VLF403212MT-100M | 900 | $4.0 \times 3.2 \times 1.2$ |
| 22 | LQH32CN220K53 | 250 | $3.2 \times 2.5 \times 1.55$ |
| 22 | LQH2MC220K02 | 185 | $2.0 \times 1.6 \times 0.9$ |
| 22 | VLF3010A-220 | 330 | $2.8 \times 2.6 \times 0.9$ |
| 22 | VLF504015MT-220M | 930 | $5.0 \times 4.0 \times 1.5$ |

## - Selection of Capacitor

Set $1 \mu \mathrm{~F}$ or more value bypass capacitor C 1 between $\mathrm{V}_{\mathrm{IN}}$ pin and GND pin as close as possible.

## R1202xxxxA/R1202xxxxB

Set $1 \mu \mathrm{~F}-4.7 \mu \mathrm{~F}$ or more capacitor C 2 between Vout and GND pin.

Table 3-A Recommended components for R1202xxxxA/R1202xxxxB

|  | Rated voltage(V) | Part No. |
| :---: | :---: | :---: |
| C1 | 6.3 | CM105B105K06 |
| C2 | 25 | GRM21BR11E105K |
| C3 | 25 | $22 p F$ |
| R1 |  | For Vout Setting |
| R2 |  | For Vout Setting |
| R3 |  | $2 \mathrm{k} \Omega$ |

If the transient drop of output voltage by the load fluctuation is large and exceeds the allowable range in above setting, refer to Table 3-B to change the capacitors of C2 and C3 for the response improvement and the transient voltage drop reduction.

Table 3-B Recommended components for R1202xxxxA/R1202xxxxB

|  | Rated voltage(V) | Part No. |
| :---: | :---: | :---: |
| C1 | 6.3 | CM105B105K06 |
| C2 | 50 | GRM31CR71H475M |
| C3 | 25 | 220 pF |
| R1 |  | For Vout Setting |
| R2 |  | For Vout Setting |
| R3 |  | $2 \mathrm{k} \Omega$ |

## R1202xxxxD

Set $0.22 \mu \mathrm{~F}$ or more capacitor C 2 between Vout and GND pin.
The rated voltage of C 2 should be 25 V or more.

Table 4 Recommended components for R1202xxxxD

|  | Rated voltage(V) | Part No. |
| :---: | :---: | :---: |
| C1 | 6.3 | CM105B105K06 |
| C2 | 25 | GRM21BR11E224 |

## - External Components Setting

If the spike noise of Vout may be large for $\mathrm{R} 1202 \times x \times x \mathrm{~A} / \mathrm{B}$, the spike noise may be picked into $\mathrm{V}_{\text {FB }}$ pin and make the operation unstable. In this case, use a R3 of the resistance value in the range from $1 \mathrm{k} \Omega$ to $5 \mathrm{k} \Omega$ to reduce a noise level of $\mathrm{V}_{\text {fb }}$.

## - The Method of Output Voltage Setting (R1202xxxxA/B)

The output voltage (Vout) can be calculated with divider resistors (R1 and R2) values as the following formula:

$$
\text { Output Voltage }\left(V_{\text {out }}\right)=V_{F B} \times(R 1+R 2) / R 1
$$

The total value of R1 and R2 should be equal or less than $300 \mathrm{k} \Omega$. Make the $\mathrm{V}_{\mathrm{I}}$ and GND line sufficient. The large current flows through the $\mathrm{V}_{\mathbb{N}}$ and $G N D$ line due to the switching. If this impedance ( $\mathrm{V}_{\mathbb{I}}$ and GND line) is high, the internal voltage of the IC may shift by the switching current, and the operating may become unstable. Moreover, when the built-in Lx switch is turn OFF, the spike noise caused by the inductor may be generated. As a result of this, recommendation voltage rating of capacitor (C2) value is equal 1.5 times larger or more than the setting output voltage.

## - LED Current setting (R1202xxxxD)

When CE pin input is "H" (Duty=100\%), LED current can be set with feedback resistor (R1)

$$
I_{\text {LED }}=V_{\text {fb }} / R 1
$$

## - LED Dimming Control (R1202xxxxD)

The LED brightness can be controlled by inputting the PWM signal to the CE pin. If the CE pin input is "L" in the fixed time (Typ. 0.5 ms ), the IC becomes the standby mode and turns OFF LEDs.
The current of LEDs can be controlled by Duty of the PWM signal of the input CE pin. The current of LEDs when High-Duty of the CE input is "Hduty" reaches the value as calculatable following formula.

$$
\text { LLed }=\text { Hduty } \times \mathrm{V}_{\text {FB }} / \mathrm{R} 1
$$

The frequency of the PWM signal is using the range between 200 Hz to 300 kHz .
When controlling the LED brightness by the PWM signal of 20 kHz or less, the increasing or decreasing of the inductor current might be make a sounds in the hearable sound wave area. In that case, please use the PWM signal in the high frequency area.


Dimming control by CE pin input

- I led accuracy (R1202xxxxD)

LED current (lLED) is affected by the offset voltage of the error amplifier in the DC/DC converter. LED might turn off due to the offset voltage variation, when brightness is controlled by low PWM duty cycle. It is recommended to input PWM signal with $10 \%$ or more duty cycle to prevented LED turn off( $\mathrm{Ta}=25^{\circ} \mathrm{C}$ ).
The table below shows the lled accuracy at low PWM duty cycle input (low brightness).
$I_{\text {LED }}$ accuracy when low PWM Duty is applied ( $\mathrm{R} 1=10 \Omega$ )

| PWM Duty applied to CE Pin | $I_{\text {LEd }}$ Min. | Leed Max. $^{(10 \% \text { (Frequency }=20 \mathrm{kHz} \text { to } 300 \mathrm{kHz} \text { ) }} 10.1 \mathrm{~mA}^{(1)}$ |
| :--- | :--- | :--- |

[^0]
## TECHNICAL NOTES

## - Current Path on PCB

The current paths in an application circuit are shown in Fig. 1 and 2.
A current flows through the paths shown in Fig. 1 at the time of MOSFET-ON, and shown in Fig. 2 at the time of MOSFET-OFF. In the paths pointed with red arrows in Fig. 2, current flows just in MOSFET-ON period or just in MOSFET-OFF period. Parasitic impedance / inductance and the capacitance of these paths influence stability of the system and cause noise outbreak. So please minimize this side effect. In addition, please shorten the wiring of other current paths shown in Fig. 1 and 2 except for the paths of LED load.

## - Layout Guide for PCB

- Please shorten the wiring of the input capacitor (C1) between Vin pin and GND pin of IC. The GND pin should be connected to the strong GND plane.
- The area of $L \times$ land pattern should be smaller.
- Please put output capacitor (C2) close to the Vout pin.
- Please make the GND side of output capacitor (C2) close to the GND pin of IC.


Fig. 1 MOSFET-ON


Fig. 2 MOSFET-OFF

- PCB Layout
- PKG:DFN1616-6B pin

R1202LxxxA/R1202LxxxB/R1202LxxxD typical board layout


- PKG: TSOT-23-6 pin

R1202NxxxA/R1202NxxxB/R1202NxxxD Typical Board Layout


[^1]
## TYPICAL CHARACTERISTICS

1) Efficiency vs. Output Current (R1202N723A)


2) Efficiency vs. Output Current (R1202N713D)


5LED, L=10 $\mu \mathrm{H}$ (LQH32CN100K53)


4LED, L=22 $\mu \mathrm{H}$ (LQH32CN220K53)


5LED, L=22 $\mu \mathrm{H}$ (LQH32CN220K53)


## 3) Efficiency vs. Output Current (R1202N713D)

$5 \mathrm{LED}, \mathrm{V}_{\mathrm{IN}}=3.6 \mathrm{~V}$

4) Output Voltage vs. Output Current (R1202N723A)



## 7) Waveform (5LED)



9) Standby Current vs. Temperature


8) Diode Forward Voltage vs. Temperature

10) Supply Current lin vs. Temperature

11) UVLO Voltage vs. Temperature


12) VFB Voltage vs. Temperature

R1202xxxxA/B

13) Switch ON Resistance RON vs. Temperature


R1202xxxxD

14) OVP Voltage vs. Temperature R1202x7xxx


## 15) Lx Limit Current vs. Temperature


18) Thermal Shutdown Detect / Release Temperature vs. Input Voltage

19) Inductor Current (output-GND short)

$$
5 L E D\left(V_{\mathbb{N}}=3 \mathrm{~V}\right)
$$

R1202N713D


5LED(Vin=3.6V)
R1202N713D


5LED( $\left.\mathrm{V}_{\mathrm{in}}=4.2 \mathrm{~V}\right)$
R1202N713D


5LED(Vin=3V)
R1202N723D


5LED(Vin=3.6V)
R1202N723D


5LED(Vin=4.2V)
R1202N723D


## 20) Load Transient Response

$\mathrm{V}_{\text {IN }}=3.6 \mathrm{~V}$, $\mathrm{V}_{\text {OUt }}=15 \mathrm{~V}$ lout $=0 \mathrm{~mA} \Leftrightarrow 30 \mathrm{~mA}$
$\mathrm{L}=10 \mu \mathrm{H}$ Setting : Table 3-A

$\mathrm{L}=22 \mu \mathrm{H} \quad$ Setting : Table 3-A


$\mathrm{L}=10 \mu \mathrm{H} \quad$ Setting : Table 3-B


$\mathrm{L}=22 \mu \mathrm{H}$ Setting: Table 3-B


The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51.

Measurement Conditions

| Item | Measurement Conditions |
| :--- | :--- |
| Environment | Mounting on Board (Wind Velocity $=0 \mathrm{~m} / \mathrm{s}$ ) |
| Board Material | Glass Cloth Epoxy Plastic (Four-Layer Board) |
| Board Dimensions | $76.2 \mathrm{~mm} \times 114.3 \mathrm{~mm} \times 0.8 \mathrm{~mm}$ |
| Copper Ratio | Outer Layer (First Layer): Less than $95 \%$ of 50 mm Square <br> Inner Layers (Second and Third Layers): Approx. $100 \%$ of 50 mm Square <br> Outer Layer (Fourth Layer): Approx. $100 \%$ of 50 mm Square |
| Through-holes | $\phi 0.2 \mathrm{~mm} \times 25$ pcs |

Measurement Result
$\left(\mathrm{Ta}=25^{\circ} \mathrm{C}, \mathrm{Tjmax}=125^{\circ} \mathrm{C}\right)$

| Item | Measurement Result |
| :--- | :---: |
| Power Dissipation | 2400 mW |
| Thermal Resistance (日ja) | $\theta \mathrm{ja}=41^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Characterization Parameter ( $\psi \mathrm{j} \mathrm{t})$ | $\psi j \mathrm{j}=11^{\circ} \mathrm{C} / \mathrm{W}$ |

Өja: Junction-to-Ambient Thermal Resistance
$\psi j$ t: Junction-to-Top Thermal Characterization Parameter


Power Dissipation vs. Ambient Temperature


Measurement Board Pattern


[^2]The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following conditions are used in this measurement.

## Measurement Conditions

| Item | Standard Test Land Pattern |
| :--- | :--- |
| Environment | Mounting on Board (Wind Velocity $=0 \mathrm{~m} / \mathrm{s}$ ) |
| Board Material | Glass Cloth Epoxy Plastic (Double-Sided Board) |
| Board Dimensions | $40 \mathrm{~mm} \times 40 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ |
| Copper Ratio | Top Side: Approx. $50 \%$ <br> Bottom Side: Approx. $50 \%$ <br> Through-holes$0.5 \mathrm{~mm} \times 44$ pcs |

Measurement Result
$\left(\mathrm{Ta}=25^{\circ} \mathrm{C}, \mathrm{Tjmax}=125^{\circ} \mathrm{C}\right)$

| Item | Standard Test Land Pattern |
| :--- | :---: |
| Power Dissipation | 460 mW |
| Thermal Resistance $(\theta j \mathrm{ja})$ | $\theta \mathrm{ja}=217^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Characterization Parameter $(\psi j \mathrm{t})$ | $\psi j \mathrm{j}=40^{\circ} \mathrm{C} / \mathrm{W}$ |

өja: Junction-to-Ambient Thermal Resistance
$\psi j$ t: Junction-to-Top Thermal Characterization Parameter


Power Dissipation vs. Ambient Temperature


Measurement Board Pattern

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UNIT: mm
TSOT-23-6 Package Dimensions

1. The products and the product specifications described in this document are subject to change or discontinuation of production without notice for reasons such as improvement. Therefore, before deciding to use the products, please refer to our sales representatives for the latest information thereon.
2. The materials in this document may not be copied or otherwise reproduced in whole or in part without the prior written consent of us.
3. This product and any technical information relating thereto are subject to complementary export controls (so-called KNOW controls) under the Foreign Exchange and Foreign Trade Law, and related politics ministerial ordinance of the law. (Note that the complementary export controls are inapplicable to any application-specific products, except rockets and pilotless aircraft, that are insusceptible to design or program changes.) Accordingly, when exporting or carrying abroad this product, follow the Foreign Exchange and Foreign Trade Control Law and its related regulations with respect to the complementary export controls.
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5. The products listed in this document are intended and designed for use as general electronic components in standard applications (office equipment, telecommunication equipment, measuring instruments, consumer electronic products, amusement equipment etc.). Those customers intending to use a product in an application requiring extreme quality and reliability, for example, in a highly specific application where the failure or misoperation of the product could result in human injury or death should first contact us.

- Aerospace Equipment
- Equipment Used in the Deep Sea
- Power Generator Control Equipment (nuclear, steam, hydraulic, etc.)
- Life Maintenance Medical Equipment
- Fire Alarms / Intruder Detectors
- Vehicle Control Equipment (automotive, airplane, railroad, ship, etc.)
- Various Safety Devices
- Traffic control system
- Combustion equipment

In case your company desires to use this product for any applications other than general electronic equipment mentioned above, make sure to contact our company in advance. Note that the important requirements mentioned in this section are not applicable to cases where operation requirements such as application conditions are confirmed by our company in writing after consultation with your company.
6. We are making our continuous effort to improve the quality and reliability of our products, but semiconductor products are likely to fail with certain probability. In order to prevent any injury to persons or damages to property resulting from such failure, customers should be careful enough to incorporate safety measures in their design, such as redundancy feature, fire containment feature and fail-safe feature. We do not assume any liability or responsibility for any loss or damage arising from misuse or inappropriate use of the products.
7. The products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this datasheet. Failure to employ the products in the proper applications can lead to deterioration, destruction or failure of the products. We shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of the products.
8. Quality Warranty

8-1. Quality Warranty Period
In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.
8-2. Quality Warranty Remedies
When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.
Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.
8-3. Remedies after Quality Warranty Period
With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.
9. Anti-radiation design is not implemented in the products described in this document.
10. The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
11. WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
12. Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
13. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.


Nisshinbo Micro Devices Inc.

## Official website

https://www.nisshinbo-microdevices.co.jp/en/

## Purchase information

https://www.nisshinbo-microdevices.co.jp/en/buy/


[^0]:    (1) Design guaranteed value $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

[^1]:    U1- indicates the position of No. 1 pin.

[^2]:    * The tab on the bottom of the package shown by blue circle is a substrate potential (GND). It is recommended that this tab be connected to the ground plane pin on the board but it is possible to leave the tab floating.

